

DATA SHEET

SKY66394-11: 2000 to 2300 MHz Wide Instantaneous Bandwidth High-Efficiency Power Amplifier

Applications

- FDD and TDD 2G/3G/4G LTE systems
- 3GPP bands 1, 4, 10, and 23 small-cell base stations
- Driver amplifier for micro-base and macro-base stations
- Active antenna array and massive MIMO

Features

- High-efficiency: PAE = 35% @ +28 dBm
- High linearity: +28 dBm with -50 dBc ACLR with pre-distortion (40 MHz LTE, 8.5 dB PAR signal)
- High gain: 38 dB
- Excellent input and output return loss: to 50Ω system
- Integrated active bias: performance compensated over temp
- Integrated enable On/Off function: PAEN = 1.7 to 2.5 V
- Single supply voltage: 5.0 V
- Pin-to-pin compatible PA family supporting all 3GPP bands
- Compact (16-pin, $5 \times 5 \times 1.3$ mm) package (MSL3, 260 °C per JEDEC J-STD-020)

Description

The SKY66394-11 is a high-efficiency fully input/output matched power amplifier (PA) with high gain and linearity. The compact 5×5 mm PA is designed for FDD and TDD 2G/3G/4G LTE small cell base stations operating from 2000 to 2300 MHz. The active biasing circuitry is integrated to compensate PA performance over temperature, voltage, and process variation.

The SKY66394-11 is part of a high-efficiency, pin-to-pin compatible PA family supporting all 3GPP bands. Table 1 lists the pin-to-pin compatible parts in the PA family.

A block diagram of the SKY66394-11 is shown in Figure 1. The device package and pinout for the device are shown in Figure 2. Signal pin assignments and functional pin descriptions are described in Table 2.

Table 1. Pin-to-Pin Compatible PA Family

| Part Number | Frequency (MHz) | 3GPP Band |
|-------------|-----------------|-----------------------------|
| SKY66391-12 | 1800 to 1900 | Bands 3 and 9 |
| SKY66399-11 | 1900 to 2000 | Bands 2, 25, 33, 36, and 37 |
| SKY66394-11 | 2000 to 2300 | Bands 1, 4, 10, and 23 |
| SKY66397-12 | 2300 to 2700 | Bands 7, 38, and 41 |



Skyworks Green™ products are compliant with all applicable legislation and are halogen-free. For additional information, refer to *Skyworks Definition of Green™*, document number SQ04-0074.

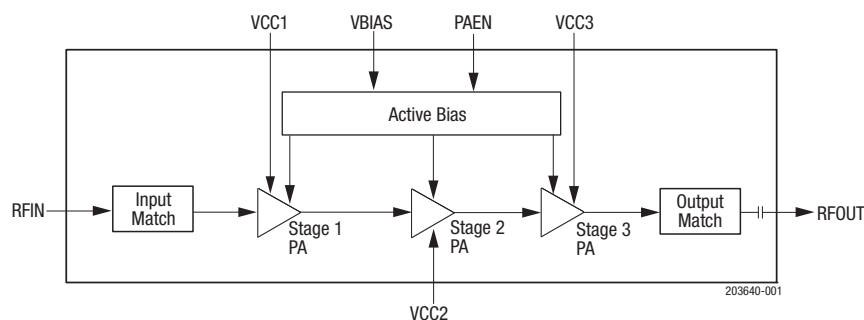


Figure 1. SKY66394-11 Block Diagram

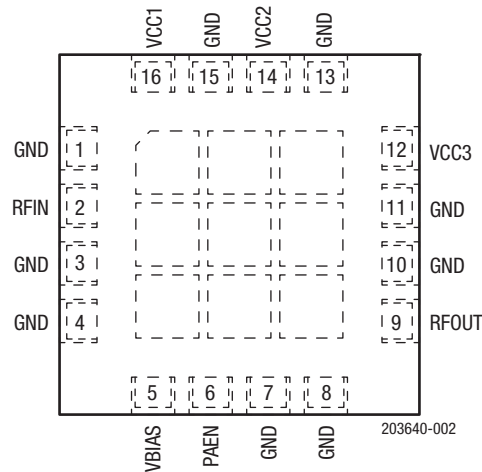


Figure 2. SKY66394-11 Pinout (Top View)

Table 2. SKY66394-11 Signal Descriptions¹

| Pin | Name | Description | Pin | Name | Description |
|-----|-------|----------------------------|-----|-------|---------------------------|
| 1 | GND | Ground | 9 | RFOUT | RF output port |
| 2 | RFIN | RF input port ² | 10 | GND | Ground |
| 3 | GND | Ground | 11 | GND | Ground |
| 4 | GND | Ground | 12 | VCC3 | Stage 3 collector voltage |
| 5 | VBIAS | Bias voltage | 13 | GND | Ground |
| 6 | PAEN | PA enable | 14 | VCC2 | Stage 2 collector voltage |
| 7 | GND | Ground | 15 | GND | Ground |
| 8 | GND | Ground | 16 | VCC1 | Stage 1 collector voltage |

¹ The center ground pad must have a low inductance and low thermal resistance connection to the application's printed circuit board ground plane.

² External DC block is required.

Technical Description

The matching circuits are contained within the device. An on-chip active bias circuit is included within the device for both input and output stages, which provides excellent gain tracking over temperature and voltage variations.

The SKY66394-11 is internally matched for maximum output power and efficiency. The input and output stages are independently supplied using the VCC1, VCC2, and VCC3 supply lines (pins 16, 14, and 12, respectively). The DC control voltage that sets the bias is supplied by the VBIAS signal (pin 5).

Electrical and Mechanical Specifications

The absolute maximum ratings of the SKY66394-11 are provided in Table 3. Recommended operating conditions are specified in Table 4 and electrical specifications are provided in Table 5.

Table 3. SKY66394-11 Absolute Maximum Ratings¹

| Parameter | Symbol | Minimum | Maximum | Units |
|--|-----------------|---------|---------|-------|
| RF input power (CW) | P _{IN} | | +8 | dBm |
| Supply voltage (VCC1, VCC2, VCC3, VBIAS) | V _{CC} | | 5.5 | V |
| PA enable | V _{EN} | | 3 | V |
| Operating temperature | T _C | -40 | +100 | °C |
| Storage temperature | T _{ST} | -55 | +125 | °C |
| Junction temperature | T _J | | +150 | °C |
| Power dissipation | P _D | | 1.9 | W |
| Device thermal resistance | θ _{JC} | | 15 | °C/W |
| Electrostatic discharge: | ESD | | | |
| Charged Device Model (CDM) | | | 500 | V |
| Human Body Model (HBM) | | | 1000 | V |

¹ Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device.

ESD HANDLING: *Although this device is designed to be as robust as possible, electrostatic discharge (ESD) can damage this device. This device must be protected at all times from ESD when handling or transporting. Static charges may easily produce potentials of several kilovolts on the human body or equipment, which can discharge without detection. Industry-standard ESD handling precautions should be used at all times.*

Table 4. SKY66394-11 Recommended Operating Conditions

| Parameter | Symbol | Min | Typ | Max | Units |
|--|--|------|-----|------|-------|
| Supply voltage (VCC1, VCC2, VCC3, VBIAS) | V _{CC1} , V _{CC2} , V _{CC3} , V _{BIAS} | 4.75 | 5 | 5.25 | V |
| PA enable: | PAEN | | | | |
| ON | | 1.7 | 2.0 | 2.5 | V |
| OFF | | | 0 | 0.5 | V |
| PA enable current | I _{ENABLE} | | 1 | 12 | μA |
| Operating frequency | f | 2110 | | 2170 | MHz |
| Operating temperature | T _C | -40 | +25 | +85 | °C |

Table 5. SKY66394-11 Electrical Specifications¹

(Vcc1 = Vcc2 = Vcc3 = VBIAS = 5 V, PAEN = 2.0 V, f = 2140 MHz, Tc = +25 °C, Input/Output Load = 50 Ω, Unless Otherwise Noted)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Units |
|---|-------------|--|-------|-------|-----|-------|
| Small signal gain | IS21l | PIN = -30 dBm | 36 | 38 | | dB |
| Gain @ +28 dBm | IS21l@28dBm | POUT = 28dBm | 36 | 38 | | dB |
| Input return loss | IS11l | PIN = -20 dBm | 12 | 16 | | dB |
| Output return loss | IS22l | PIN = -20 dBm | 10 | 14 | | dB |
| Reverse isolation ² | IS12l | PIN = -30 dBm | | 50 | | dB |
| ACLR @ +28 dBm | ACLR | POUT = +28 dBm (40 MHz LTE, 8.5 dB PAR signal) | | -28.5 | -27 | dBc |
| Saturated output power | PSAT | CW, PIN = +5 dBm | +35.5 | +36.3 | | dBm |
| Output power at 3dB gain compression ³ | P3dB | CW, reference to Gain @ +28 dBm | +34.5 | +35.3 | | dBm |
| 2 nd harmonic | 2fo | CW, POUT = +28 dBm | | -29 | -25 | dBc |
| 3 rd harmonic | 3fo | CW, POUT = +28 dBm | | -63 | -55 | dBc |
| Power-added efficiency | PAE | CW, POUT = +28 dBm | 32 | 35 | | % |
| Quiescent current | Iccq | No RF signal | | 105 | 135 | mA |

¹ Performance is guaranteed only under the conditions listed in this table.

² Not test in production. Verified by design.

³ Refer to the performance plot in Figure 7.

Typical Performance Characteristics

(Vcc1 = Vcc2 = Vcc3 = VBIAS = 5 V, PAEN = 2.0 V, f = 2140 MHz, Tc = +25 °C, Unless Otherwise Noted)

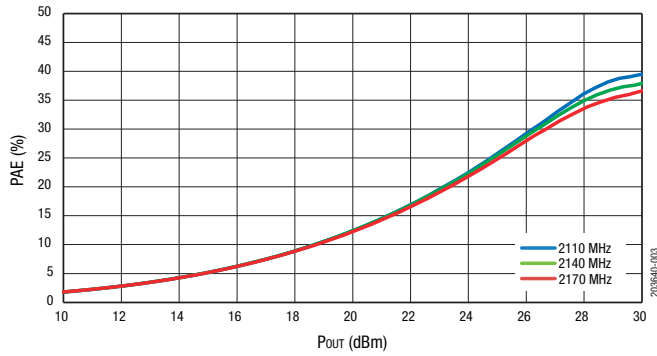


Figure 3. PAE vs Pout Across Frequency

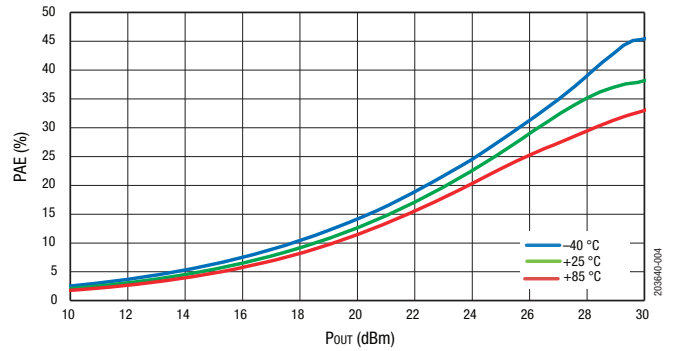


Figure 4. PAE vs Pout Across Temperature

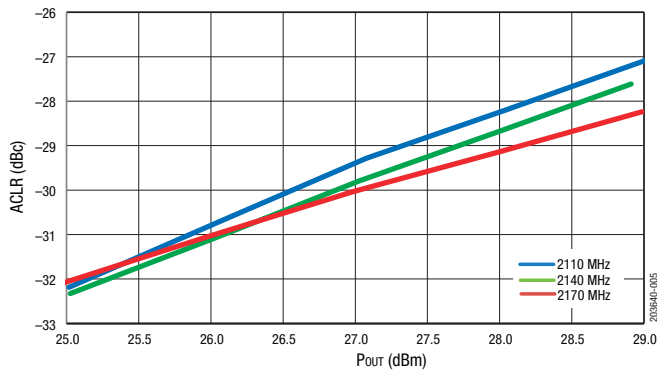


Figure 5. ACLR vs. Pout Across Frequency (40 MHz LTE, 8.5 dB PAR Signal)

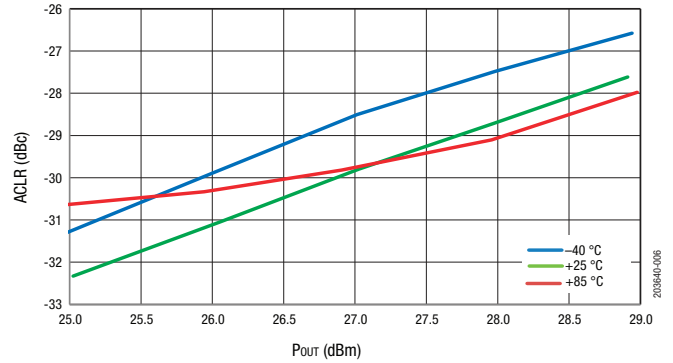


Figure 6. ACLR vs Pout Across Temperature (40 MHz LTE, 8.5 dB PAR Signal)

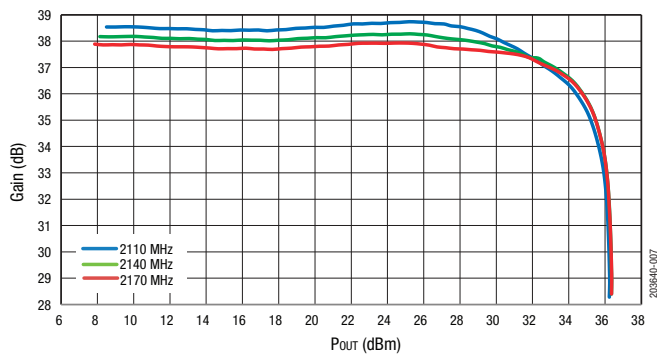


Figure 7. Gain vs Pout Across Frequency

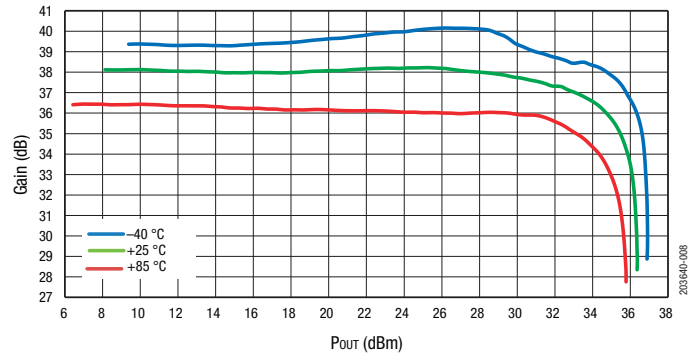


Figure 8. Gain vs Pout Across Temperature

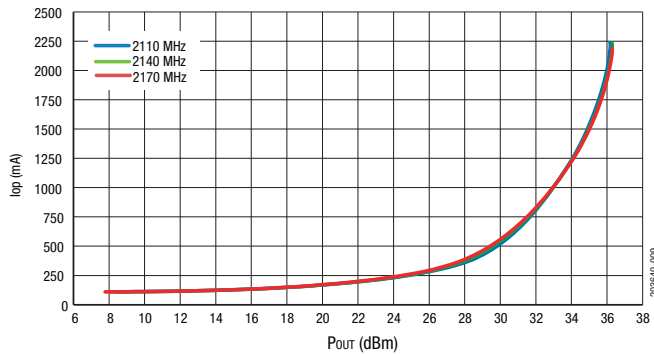


Figure 9. Operating Current vs Pout Across Frequency

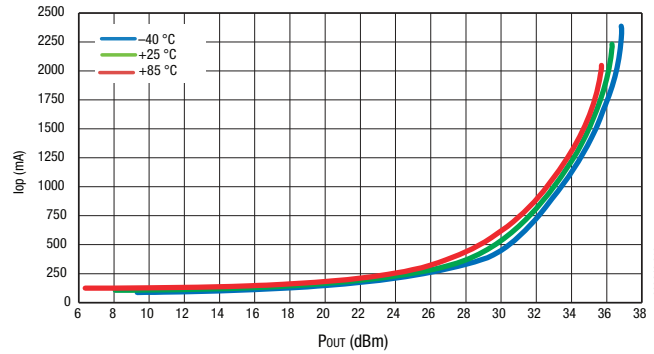


Figure 10. Operating Current vs Pout Across Temperature

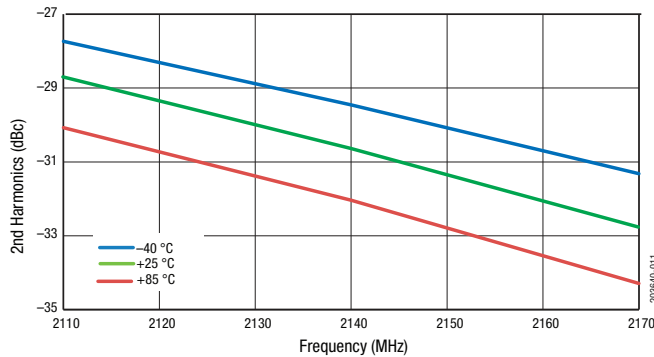


Figure 11. 2nd Harmonic vs Frequency Across Temperature @ Pout = +28 dBm (CW)

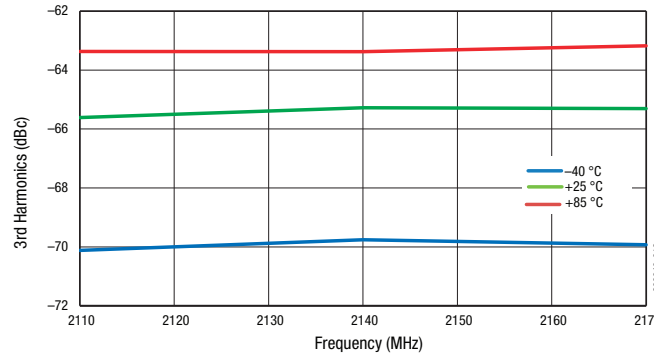


Figure 12. 3rd Harmonic vs Frequency Across Temperature @ Pout = +28 dBm (CW)

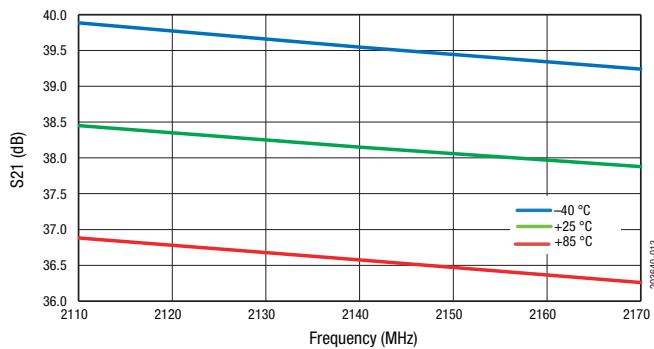


Figure 13. Small Signal Gain vs Frequency Across Temperature (Pin = -30 dBm)

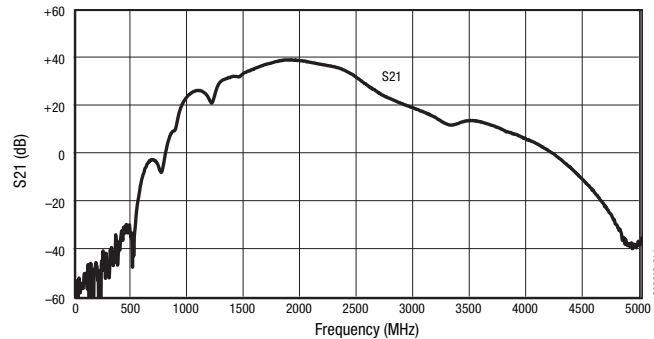


Figure 14. Wide Band Small Signal Gain vs Frequency (Pin = -30 dBm)

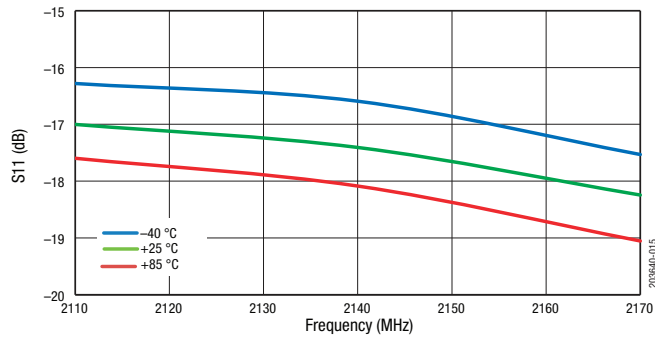


Figure 15. Input Return Loss vs Frequency Across Temperature (Small Signal, P_{IN} = -20 dBm)

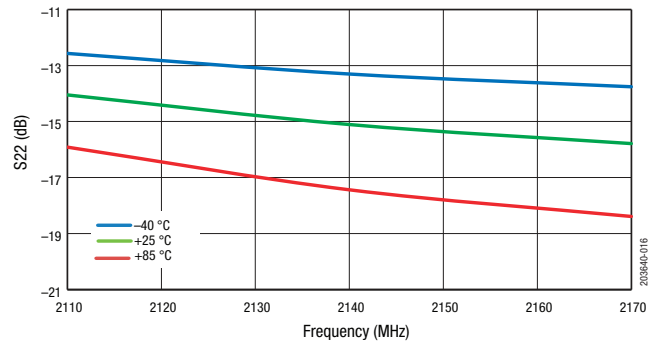


Figure 16. Output Return Loss vs Frequency Across Temperature (Small Signal, P_{IN} = -20 dBm)

Evaluation Board Description

The SKY66394-11 Evaluation Board is used to test the performance of the SKY66394-11 PA. An application schematic is provided in Figure 17. Table 6 provides the Bill of Materials (BOM) list for Evaluation Board components.

An assembly drawing for the Evaluation Board is shown in Figure 18. Board layer details are shown in Figure 19. Layer detail physical characteristics are noted in Figure 20.

Circuit Design Considerations

The following design considerations are general in nature and must be followed regardless of final use or configuration:

- Paths to ground should be made as short as possible.
- The ground pad of the SKY66394-11 has special electrical and thermal grounding requirements. This pad is the main thermal conduit for heat dissipation. Because the circuit board acts as the heat sink, it must shunt as much heat as possible from the device.

Therefore, design the connection to the ground pad to dissipate the maximum wattage produced by the circuit board. Multiple vias to the grounding layer are required.

NOTE: A poor connection between the ground pad and ground increases junction temperature (T_j), which reduces the life of the device.

Evaluation Board Test Procedure

Turn-On Sequence

1. Connect 50 Ω test equipment or load to the input and output RF ports of the Evaluation Board.
2. Connect the DC ground.
3. Connect all VCCs and VBIAS lines to a +5 V supply. Connect PAEN to a 2.0 V supply.
4. Without applying RF, turn on the 5 V supply, then turn on the 2 V PAEN.
5. Apply RF signal –30 dBm and observe that the gain of the device is approximately 38 dB. Begin measurements.

Turn-Off Sequence

1. Turn off the RF input to the device.
2. Turn off PAEN (set to 0 V).
3. Turn off all VCCs and VBIAS.

NOTE: It is important to adjust the VCC voltage sources so that +5 V is measured at the board. High collector currents drop the collector voltage significantly if long leads are used. Adjust the bias voltage to compensate.

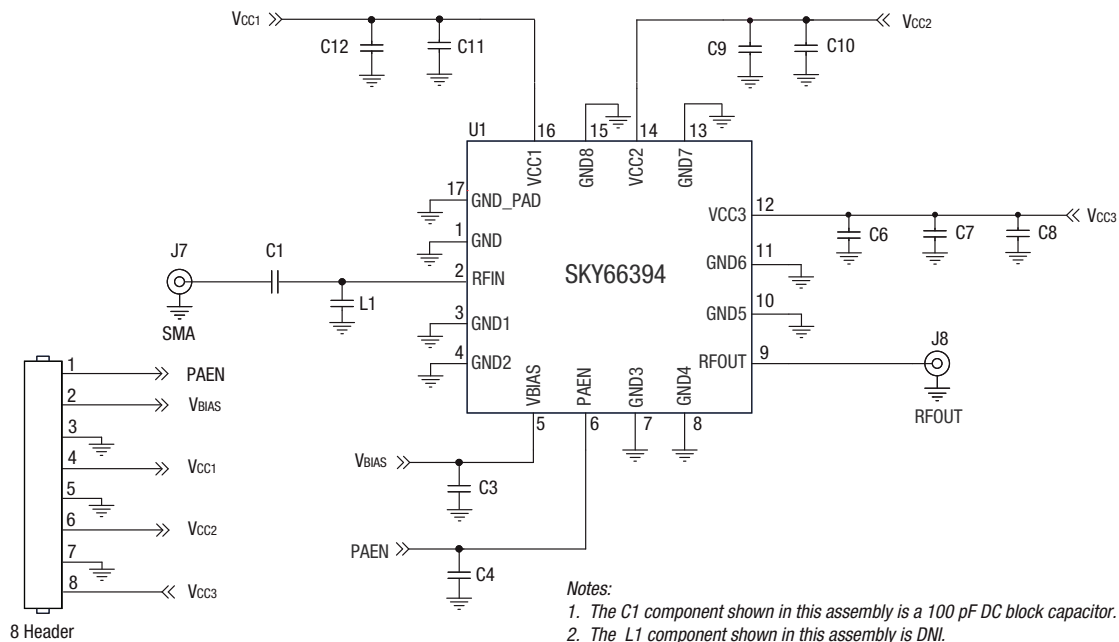
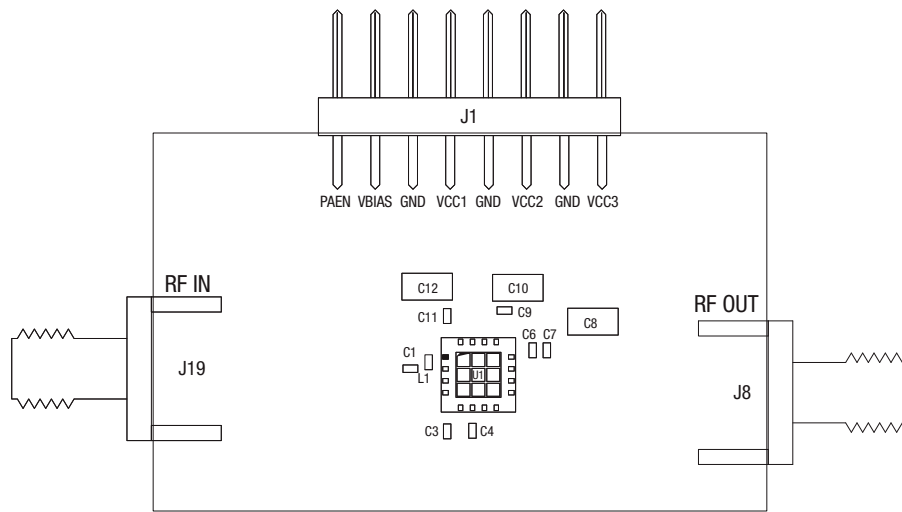


Figure 17. SKY66394-11 Application Schematic

203640-017

Table 6. SKY66394-11 Evaluation Board Bill of Materials (BOM)

| Component | Description | Size |
|----------------|---|------|
| C1 | Ceramic capacitor, 100 pF | 0402 |
| C3 | Ceramic capacitor, 1 μ F, \pm 10%, 16 V | 0402 |
| C4, C7 | Ceramic capacitor, 3300 pF, X7R, \pm 10%, 50 V | 0402 |
| C6, C9, C11 | Ceramic capacitor, 0.22 μ F | 0402 |
| C8, C10, C12 | Ceramic capacitor, 10 μ F, X7R, \pm 10%, 16 V | 1206 |
| L1 | DNI | DNI |
| TW21-D690-xxxx | Evaluation Board | - |



Notes:
 1. Evaluation Board Gerber files are available on request.
 2. The L1 component shown in this assembly is DNI.

Figure 18. Evaluation Board Assembly Drawing

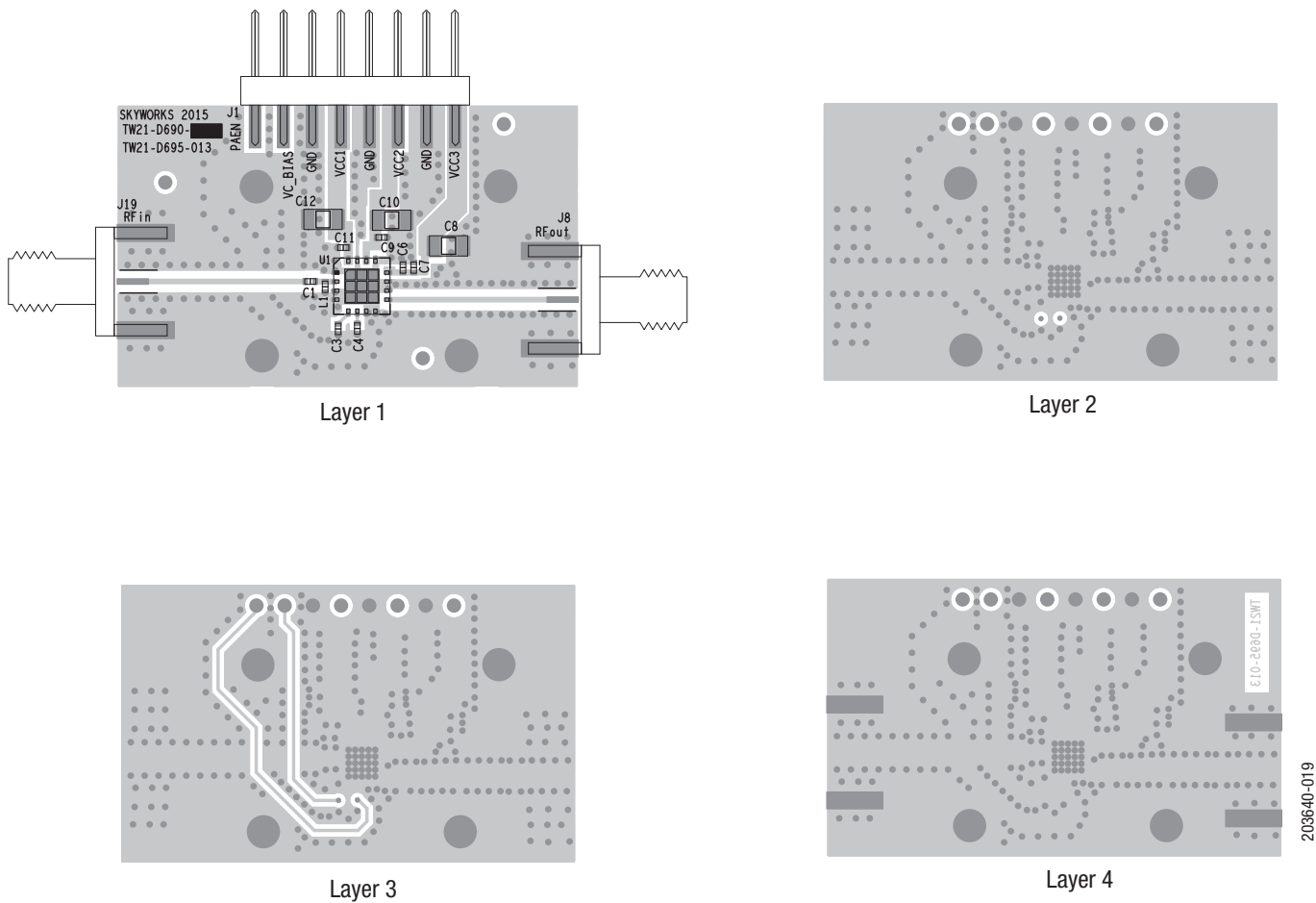


Figure 19. Board Layer Detail

| 50 Ohm | Cross Section | Name | Thickness (mm) | Materials |
|------------------|---------------|------------|----------------|---------------|
| W = 0.500 mm | | TMask | 0.010 | Solder Resist |
| | | L1 | 0.035 | Cu, 1 oz. |
| | | Dielectric | : 0.250 | R04350 |
| | | L2 | 0.035 | Cu, 1 oz. |
| | | Dielectric | : 0.350 | FR4 |
| | | L3 | 0.035 | Cu, 1 oz. |
| | | Dielectric | : 0.250 | FR4 |
| | | L4 | 0.035 | Cu, 1 oz. |
| | | BMask | 0.010 | Solder Resist |

203640-020

Figure 20. Layer Detail Physical Characteristics

Application Circuit Notes

Center Ground. It is extremely important to sufficiently ground the bottom ground pad of the device for both thermal and stability reasons. Multiple small vias are acceptable and work well under the device if solder migration is an issue.

GND (pins 1, 3, 4, 7, 8, 10, 11, 13, and 15). Attach all ground pins to the RF ground plane with the largest diameter and lowest inductance via that the layout allows. Multiple small vias are acceptable and will work well under the device if solder migration is an issue.

VCBIAS (pin 5). The bias supply voltage for each stage, nominally set to +5 V.

RFOUT (pin 9). Amplifier RF output pin ($Z_0 = 50 \Omega$). The module includes an internal DC blocking capacitor. All impedance matching is provided internal to the module.

VCC1, VCC2, and VCC3 (pin 16, 15, and 12, respectively). Supply voltage for each stage collector bias is nominally set to 5 V. Bypass and decoupling capacitors C6 through C12 should be placed in the approximate location shown on the evaluation board assembly drawing, although exact placement is not critical.

RFIN (pin 2). Amplifier RF input pin ($Z_0 = 50 \Omega$). All impedance matching is provided internal to the module. DC block C1 should be placed in the approximate location shown on the Evaluation Board assembly drawing.

Package Dimensions

Typical part marking for the device is shown in Figure 21. The PCB layout footprint for the SKY66394-11 is shown in Figure 22. Package dimensions are shown in Figure 23, and tape and reel dimensions are provided in Figure 24.

Package and Handling Information

Since the device package is sensitive to moisture absorption, it is baked and vacuum packed before shipping. Instructions on the shipping container label regarding exposure to moisture after the container seal is broken must be followed. Otherwise, problems related to moisture absorption may occur when the part is subjected to high temperature during solder assembly.

The SKY66394-11 is rated to Moisture Sensitivity Level 3 (MSL3) at 260 °C. It can be used for lead or lead-free soldering. For additional information, refer to Skyworks Application Note, *PCB Design and SMT Assembly/Rework Guidelines for MCM-L Packages*, document number 101752.

Care must be taken when attaching this product, whether it is done manually or in a production solder reflow environment. Production quantities of this product are shipped in a standard tape and reel format.

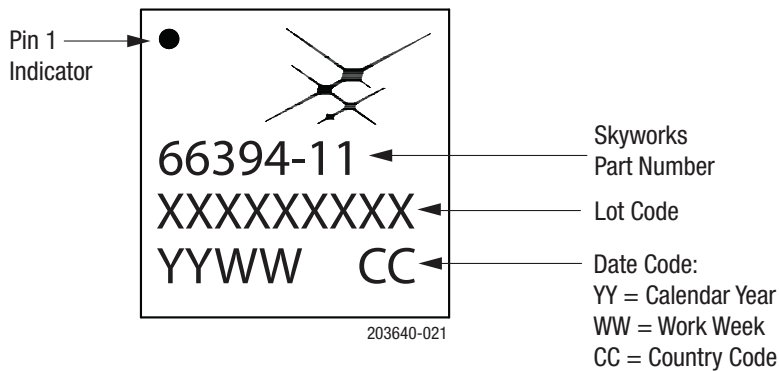


Figure 21. SKY66394-11 Typical Part Marking

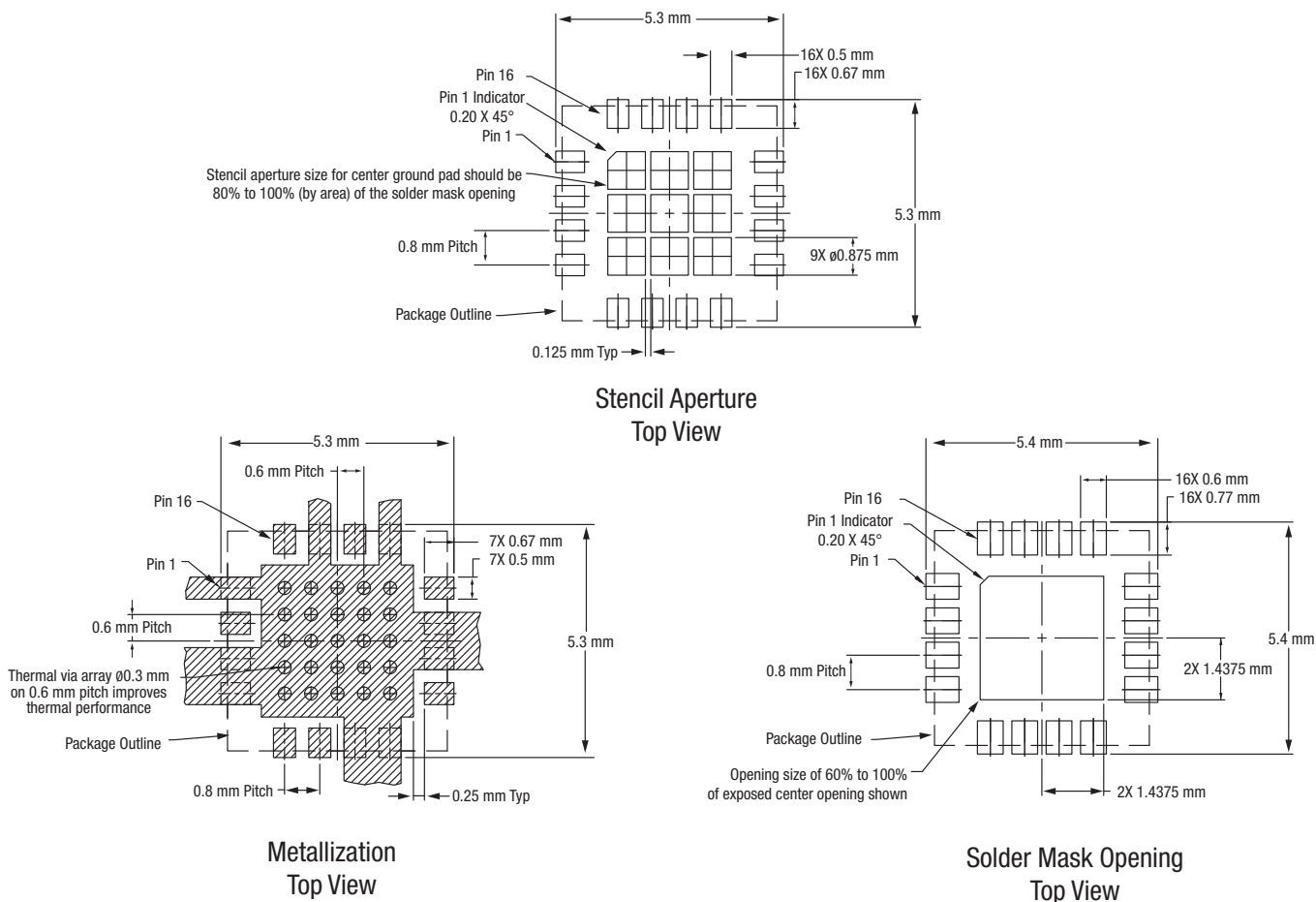


Figure 22. SKY66394-11 PCB Layout Footprint

Notes:

1. Thermal vias should be resin filled and capped in accordance with IPC-4761 type VII vias.
2. Recommended Cu thickness is 30 to 35 μm .

203640-022

